

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)
2. (Currently Amended) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:

a polymer compound produced by addition polymerization having an epoxy ~~group and group~~;

a compound with a molecular weight of 2000 or less having at least two carboxyl groups, or protected carboxyl ~~groups, and groups~~; and

a solvent, ~~wherein at least one of the polymer compound and the compound has a s-triazine trione skeleton.~~

3. (Currently Amended) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:

~~a compound~~ an s-triazine trione skeleton compound with a molecular weight of 2000 or less having at least two epoxy ~~groups and groups~~;

a polymer compound having a phenolic hydroxyl group, a carboxyl group, a protected carboxyl group or an acid anhydride ~~structure, and structure~~; and

a solvent, ~~wherein at least one of the compound and the polymer compounds has a s-triazine trione skeleton.~~

4. (Currently Amended) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:

a solvent, ~~and solvent; and~~

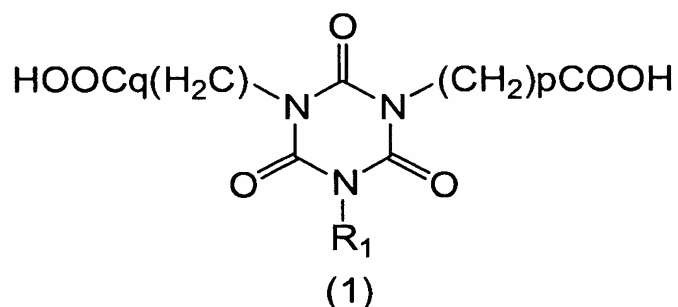
a polymer compound having a carboxyl group or a protected carboxyl group, an epoxy group, ~~and a s-triazine trione skeleton.~~

5. (Currently Amended) The underlayer coating forming composition according to ~~claim 1 or~~ claim 3, wherein the polymer compound having a carboxyl group is a compound having acrylic acid or methacrylic acid as a unit structure.

6. (Currently Amended) The underlayer coating forming composition according to ~~claim 1 or~~ claim 3, wherein the polymer compound having a phenolic hydroxyl group is a compound having hydroxystyrene as a unit structure.

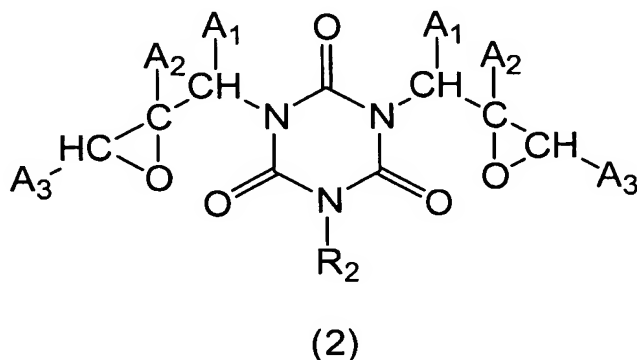
7. (Original) The underlayer coating forming composition according to claim 3, wherein the compound with a molecular weight of 2000 or less having at least two epoxy groups is a compound having at least three epoxy groups and no aromatic ring structure.

8. (Original) The underlayer coating forming composition according to claim 2, wherein the compound with a molecular weight of 2000 or less having at least two carboxyl groups is a compound of formula (1)

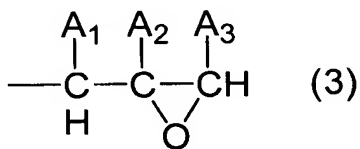


wherein p and q is a number of 1 to 6, R₁ is hydrogen atom, C₁₋₆ alkyl group, C₃₋₆ alkenyl group, benzyl group, phenyl group or -(CH₂)_rCOOH wherein r is a number of 1 to 6.

9. (Original) The underlayer coating forming composition according to claim 3, wherein the compound with a molecular weight of 2000 or less having at least two epoxy groups is a compound of formula (2)



wherein A₁, A₂ and A₃ each are hydrogen atom, methyl group or ethyl group, R₂ is hydrogen atom, C₁₋₆ alkyl group, C₃₋₆ alkenyl group, benzyl group, phenyl group or a group of formula (3)



10. (Canceled)

11. (Currently Amended) The underlayer coating forming composition according to ~~claim 1~~claim 2, further comprising a light absorbing compound.

12. (Currently Amended) A method for forming an underlayer coating for use in manufacture of semiconductor device, comprising coating the underlayer coating forming composition according to ~~claim 1~~claim 2.

13. (Currently Amended) A method for forming photoresist pattern for use in manufacture of semiconductor device, comprising

coating the underlayer forming composition according to ~~claim 1~~claim 2 on a semiconductor substrate, and baking it to form an underlayer coating,

forming a photoresist layer on the underlayer coating,

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light, and

developing the photoresist layer after the exposure to light.

14. (Original) The method for forming photoresist pattern according to claim 13, wherein the exposure to light is carried out with a light of a wavelength of 248 nm, 193 nm or 157 nm.